Silicon Controlled Rectifiers Reverse Blocking Thyristors

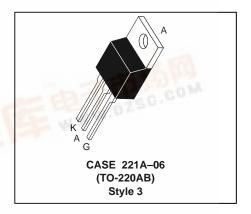
Designed primarily for half-wave ac control applications, such as motor controls, heating controls, and power supplies; or wherever half-wave, silicon gate-controlled devices are needed.

- Blocking Voltage to 800 Volts
- On-State Current Rating of 16 Amperes RMS
- High Surge Current Capability 160 Amperes
- Industry Standard TO–220AB Package for Ease of Design
- Glass Passivated Junctions for Reliability and Uniformity

MCR16 SERIES'

*Motorola preferred devices

SCRs 16 AMPERES RMS 400 thru 800 VOLTS



MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

erred devices are Motorola recommended choices for future use and best overall value.

Parameter	Symbol	Value	Unit Volts
Peak Repetitive Off-State Voltage (1) Peak Repetitive Reverse Voltage (T _J = -40 to 125°C) MCR16D MCR16M MCR16N	VDRM VRRM	400 600 800	
On-State RMS Current (All Conduction Angles)	I _{T(RMS)}	16	А
Peak Non-repetitive Surge Current (One Half Cycle, 60 Hz, T _J = 125°C)	ITSM	160	А
Circuit Fusing Consideration (t = 8.3 ms)	l ² t	106	A ² sec
Peak Gate Power (Pulse Width ≤ 1.0 µs, T _C = 80°C)	P _{GM}	5.0	Watts
Average Gate Power (t = 8.3 ms, T _C = 80°C)	P _G (AV)	0.5	Watts
Peak Gate Current (Pulse Width ≤ 1.0 μs, T _C = 80°C)	IGM	2.0	А
Operating Junction Temperature Range	TJ	-40 to +125	°C
Storage Temperature Range	T _{stg}	-40 to +150	°C

THERMAL CHARACTERISTICS

Thermal Resistance — Junction to Case — Junction to Ambient	R _Ð JC R _Ð JA	1.5 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	T_L	260	°C

⁽¹⁾ VDRM and VRRM for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS						
$\begin{tabular}{lll} Peak Forward Blocking Current & T_J = 25^\circ C \\ Peak Reverse Blocking Current & T_J = 125^\circ C \\ (V_{AK} = Rated V_{DRM} \mbox{ or } V_{RRM}, \mbox{ Gate Open}) & \end{tabular}$	I _{DRM} IRRM	_		0.01 2.0	mA	
ON CHARACTERISTICS	•		•			
Peak On-State Voltage* (I _{TM} = 32 A)	V _{TM}	_	_	1.7	Volts	
Gate Trigger Current (Continuous dc) ($V_D = 12 \text{ V}, R_L = 100 \Omega$)	IGT	2.0	8.0	20	mA	
Gate Trigger Voltage (Continuous dc) ($V_D = 12 \text{ V}, R_L = 100 \Omega$)		0.5	0.65	1.0	Volts	
Hold Current (Anode Voltage =12 V)		4.0	25	40	mA	
DYNAMIC CHARACTERISTICS	•	-		-		
Critical Rate of Rise of Off–State Voltage (V _D = Rated V _{DRM} , Exponential Waveform, Gate Open, T _J = 25°C)	dv/dt	50	200	_	V/µs	

^{*}Indicates Pulse Test: Pulse Width \leq 2.0 ms, Duty Cycle \leq 2%.

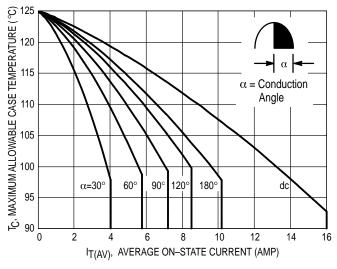


Figure 1. Average Current Derating

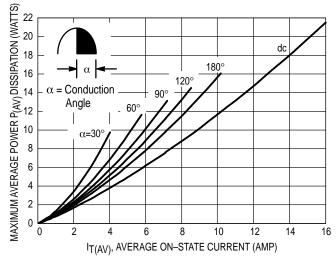


Figure 2. Maximum On-State Power Dissipation

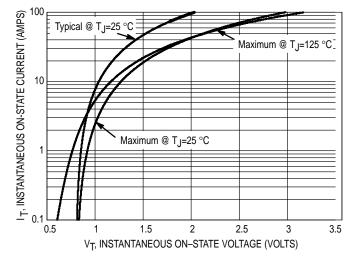


Figure 3. On-State Characteristics

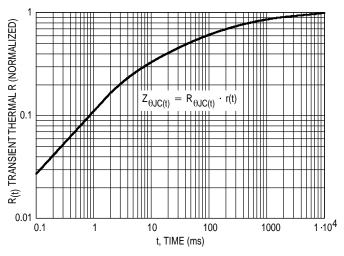


Figure 4. Transient Thermal Response

MCR16 SERIES

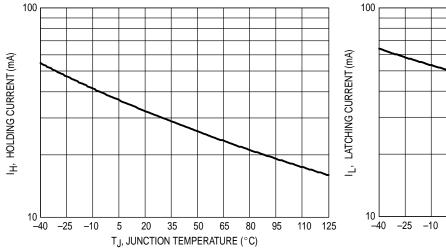


Figure 5. Typical Holding Current Versus **Junction Temperature**

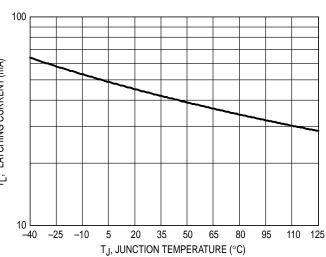


Figure 6. Typical Latching Current Versus Junction Temperature

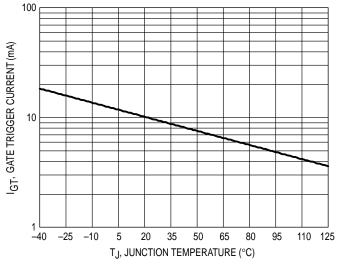


Figure 7. Typical Gate Trigger Current Versus **Junction Temperature**

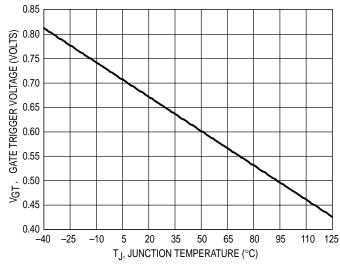


Figure 8. Typical Gate Trigger Voltage Versus **Junction Temperature**

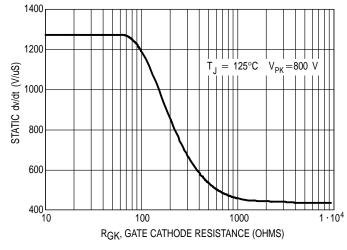


Figure 9. Typical Exponential Static dv/dt Versus Gate Cathode Resistance.

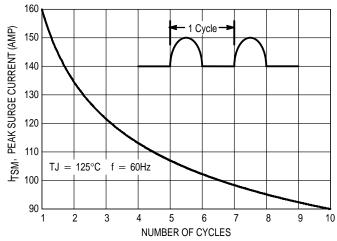
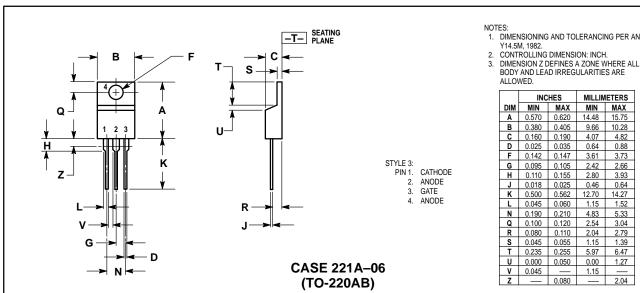


Figure 10. Maximum Non-Repetitive **Surge Current**

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PACKAGE DIMENSIONS



- DIMENSIONING AND TOLERANCING PER ANSI
- BODY AND LEAD IRREGULARITIES ARE

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.570	0.620	14.48	15.75	
В	0.380	0.405	9.66	10.28	
С	0.160	0.190	4.07	4.82	
D	0.025	0.035	0.64	0.88	
F	0.142	0.147	3.61	3.73	
G	0.095	0.105	2.42	2.66	
Н	0.110	0.155	2.80	3.93	
J	0.018	0.025	0.46	0.64	
K	0.500	0.562	12.70	14.27	
L	0.045	0.060	1.15	1.52	
N	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.39	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
٧	0.045		1.15		
Z		0.080		2.04	

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